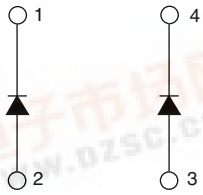
HEXFRED®
Ultrafast Soft Recovery Diode, 120 A

SOT-227



FEATURES

- Fast recovery time characteristic
- Electrically isolated base plate
- Large creepage distance between terminal
- Simplified mechanical designs, rapid assembly
- UL pending
- Totally lead (Pb)-free
- Designed and qualified for industrial level

Pb-free RoHS COMPLIANT

DESCRIPTION/APPLICATIONS

The dual diode series configuration (HFA120FA120P) is used for output rectification or freewheeling/clamping operation and high voltage application.
The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.
These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

PRODUCT SUMMARY	
V_R	1200 V
V_F (typical)	2.8 V
t_{rr} (typical)	145 ns
$I_{F(DC)}$ at T_C	60 A at 62 °C

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Cathode to anode voltage	V_R		1200	V
Continuous forward current	I_F	T_C = 62 °C	60	A
Single pulse forward current	I_{FSM}	T_J = 25 °C	350	
Maximum repetitive forward current	I_{FRM}	Rated V_R, square wave, 20 kHz, T_C = 60 °C	130	
Maximum power dissipation	P_D	T_C = 25 °C	337	W
		T_C = 100 °C	135	
RMS isolation voltage	V_{ISOL}	Any terminal to case, t = 1 minute	2500	V
Operating junction and storage temperature range	T_J, T_{Stg}		- 55 to + 150	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I_R = 100 µA	1200	-	-	V
Forward voltage	V_{FM}	I_F = 60 A	-	2.8	4.0	
		I_F = 120 A	-	3.6	5.3	
		I_F = 60 A, T_J = 125 °C	-	2.7	-	
Reverse leakage current	I_{RM}	V_R = V_R rated	-	2.0	75	µA
		T_J = 150 °C, V_R = V_R rated	-	2.7	10	mA

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)							
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**MIN.**	**TYP.**	**MAX.**	**UNITS**
Reverse recovery time	t_{rr}	T_J = 25 °C	I_F = 50 A dI_F/dt = - 200 A/µs V_R = 200 V	-	145	-	ns
		T_J = 125 °C		-	218	-	
Peak recovery current	I_{RRM}	T_J = 25 °C		-	13	-	A
		T_J = 125 °C		-	18	-	
Reverse recovery charge	Q_{rr}	T_J = 25 °C		-	910	-	nC
		T_J = 125 °C		-	1920	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNITS**
Junction to case, single leg conducting	R_{thJC}		-	-	0.37	°C/W
Junction to case, both legs conducting			-	-	0.185	
Case to heatsink	R_{thCS}	Flat, greased and surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque			-	1.3	-	Nm

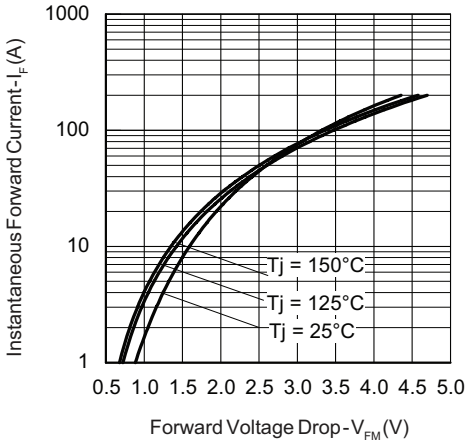


Fig. 1 - Typical Forward Voltage Drop Characteristics

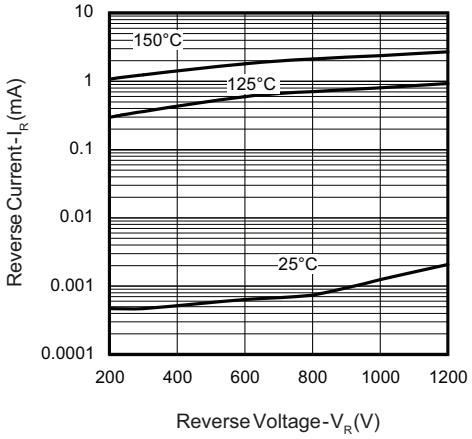


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

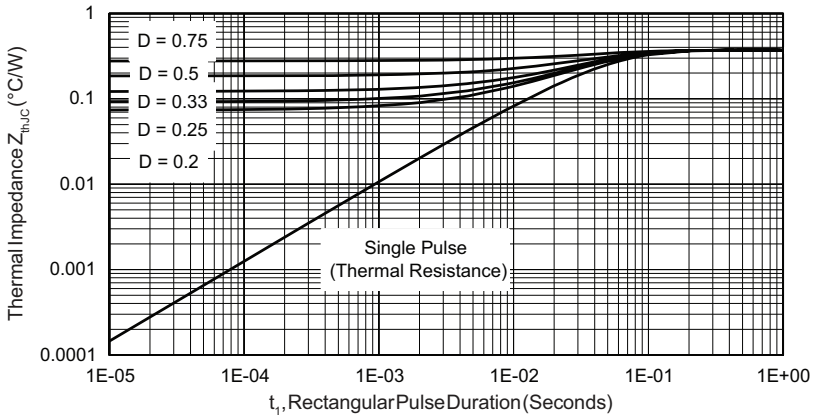


Fig. 3 - Maximum Thermal Impedance Z_{thJC} Characteristics

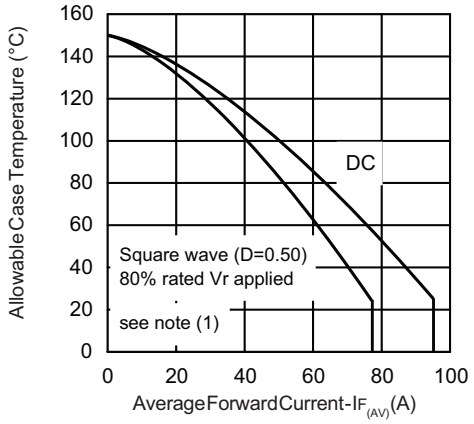


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

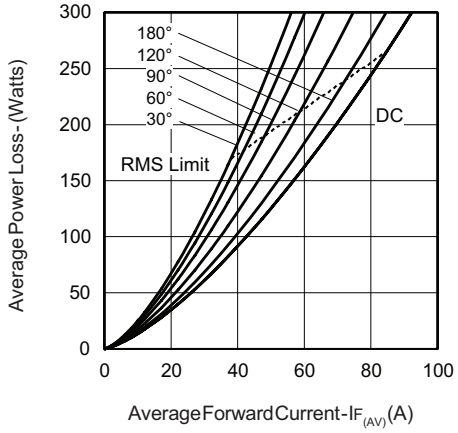


Fig. 5 - Forward Power Loss Characteristics

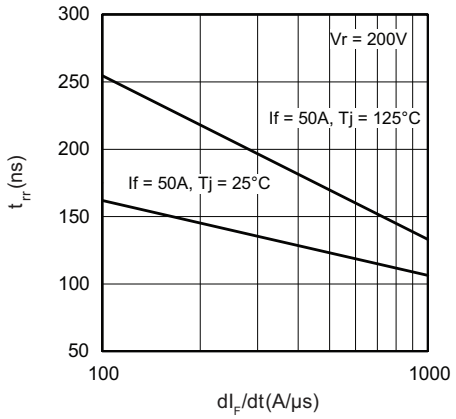


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

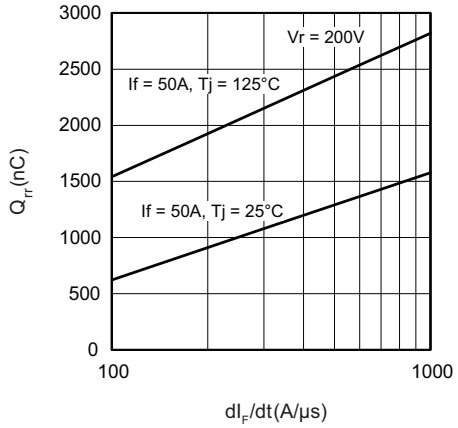


Fig. 7 - Typical Stored Charge vs. dI_F/dt

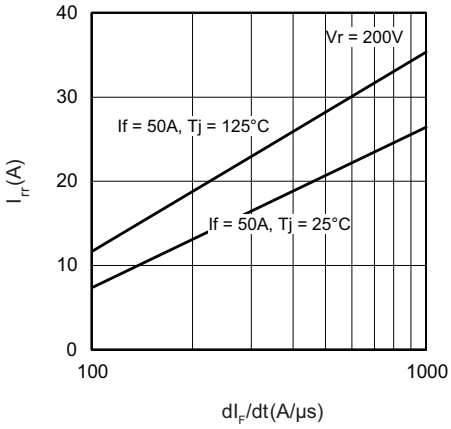


Fig. 8 - Typical Peak Recovery Current vs. dI_F/dt

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}$/D) (see fig. 5);
Pd_{REV} = Inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = Rated V_R

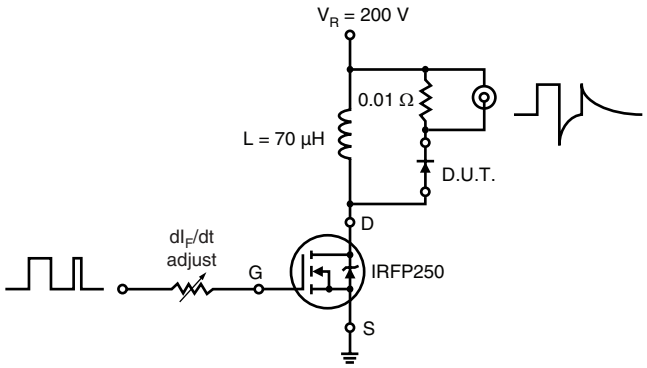
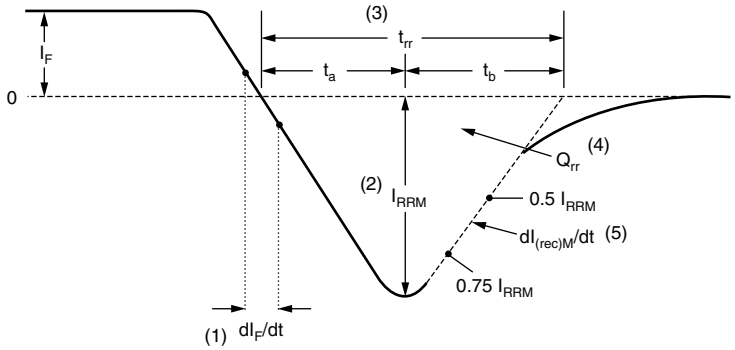


Fig. 9 - Reverse Recovery Parameter Test Circuit



(1) dI_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

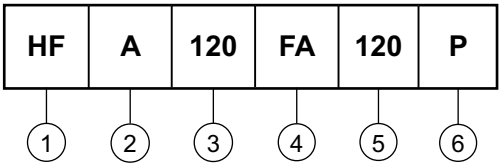
HFA120FA120P

Vishay High Power Products

HEXFRED®
Ultrafast Soft Recovery
Diode, 120 A

ORDERING INFORMATION TABLE

Device code



1 - HEXFRED® family
2 - Process designator (A = Electron irradiated)
3 - Average current (120 = 120 A)
4 - Package outline (FA = SOT-227)
5 - Voltage rating (120 = 1200 V)
6 - P = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95036
Packaging information	http://www.vishay.com/doc?95037

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